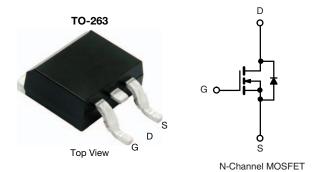


Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	100	
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0059	
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0080	
I _D (A)	75	
Configuration	Single	
Package	TO-263	



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25 ^{\circ}C$ a	1	75	
Continuous Drain Current	T _C = 125 °C	l _D	67	
Continuous Source Current (Diode Conduction) a		I _S	75	Α
Pulsed Drain Current b		I _{DM}	180	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	60	
Single Pulse Avalanche Energy	L=U.I MH	E _{AS}	180	mJ
Mariana Baran Biratan b	T _C = 25 °C	P _D	166	W
Maximum Power Dissipation ^b	T _C = 125 °C		55	VV
Operating Junction and Storage Temperatu	re Range	T _J , T _{stq}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB mount c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.9	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).



www.vishay.com

Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					L	L	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nΑ
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	500	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	50	-	-	Α
		V _{GS} = 10 V	I _D = 30 A	-	0.0046	0.0059	
Drain Course On State Resistance 8		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0099	Ω
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0123	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0056	0.0080	
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 25 A	-	95	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	4170	5500	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	1935	2600	pF
Reverse Transfer Capacitance	C _{rss}			-	160	220	
Total Gate Charge ^c	Qg			-	66	100	
Gate-Source Charge c	Q _{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 50 \text{ V}, I_{D} = 50 \text{ A}$	-	14	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	12	-	
Gate Resistance	R_g		f = 1 MHz	0.90	1.92	3	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	13	25	
Rise Time ^c	t _r	V _{DD} =	= 50 V, R _L = 1.08 Ω	-	21	35	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A},$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	34	60	ns
Fall Time ^c	t _f			-	13	25	
Source-Drain Diode Ratings and Chara	icteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	180	Α
Forward Voltage	V _{SD}	I _F = 50 A, V _{GS} = 0		-	0.90	1.5	V

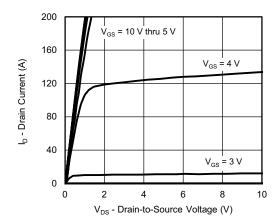
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

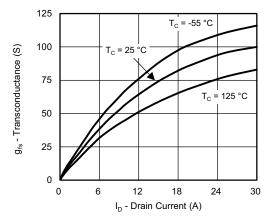
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



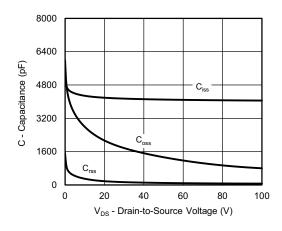
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



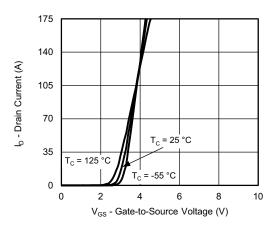
Output Characteristics



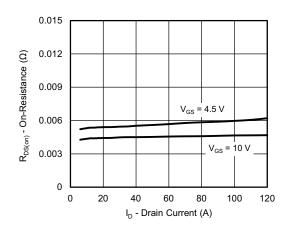
Transconductance



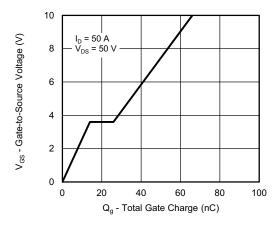
Capacitance



Transfer Characteristics



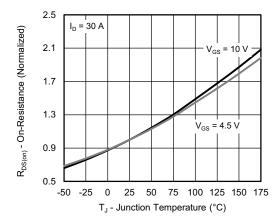
On-Resistance vs. Drain Current



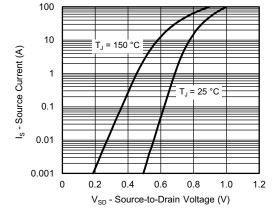
Gate Charge



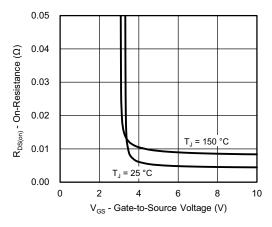
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



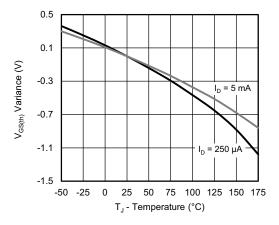
On-Resistance vs. Junction Temperature



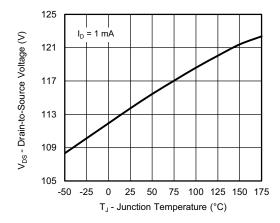
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



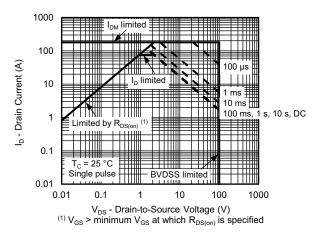
Threshold Voltage



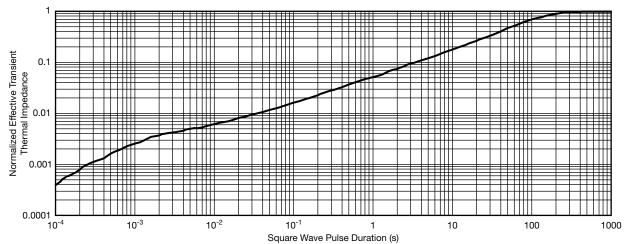
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



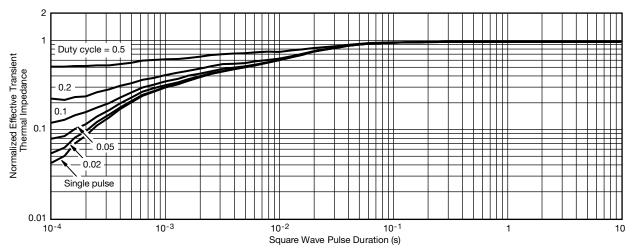
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

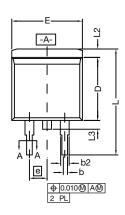
- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

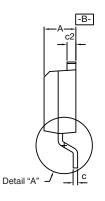
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67764.

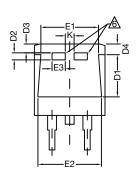
Vishay Siliconix

TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T









DETAIL A (ROTATED 90°)



≥ <u>↓</u>			ţ
< T		[C]	ပ
SF	CTION	1	1

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

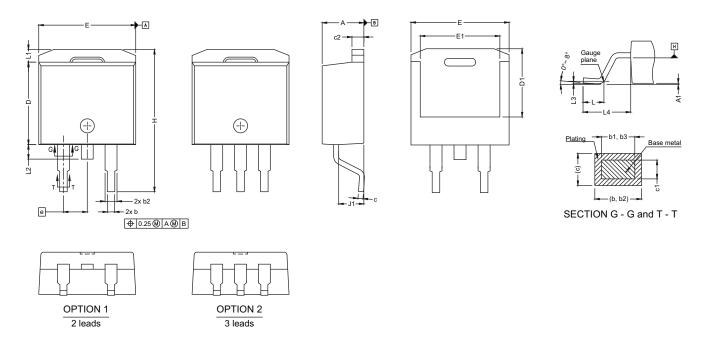
		INCHES		MILLIN	METERS
DIM.		MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
C*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	<u>E1</u>	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	BSC	2.54	BSC
K		0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
	L1	0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010) BSC	0.254	BSC
	М	-	0.002	-	0.050



www.vishay.com

Vishay Siliconix

VERSION 2: FACILITY CODE = N



DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
С	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
е	2.54	BSC
Н	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25 typ.	
L4	4.78	5.28
J1	2.56	2.96

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.